

Neifeld Ref: OSEM-DB3

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Walter David BRADDOCK

INT APP. NO: 09/636,484

FILED: 8/10/2000

FOR: Integrated Transistor Devices

GAU: 2811

EXAMINER: Donghee KANG

PTO Confirmation. No. 6691

**37 CFR 1.97 INFORMATION DISCLOSURE STATEMENT**

ASSISTANT COMMISSIONER FOR PATENTS  
ALEXANDRIA, VA 22313

SIR:

Applicant(s) wish to disclose the following information.

**REFERENCES**

- ☒ The applicant(s) wish to make of record the references listed on the attached PTO-1449. Copies of the listed references are being submitted herewith or, were submitted in the parent or grandparent application, where required, as were either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references, or cited by the examiner.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

**RELATED CASES**

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

**CERTIFICATION**

- ☐ Each item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

**PETITION**

- ☐ Applicant(s) hereby request consideration of the attached information. A check is attached in the amount of the Petition fee required under 37 CFR §1.17(p).

**DEPOSIT ACCOUNT**

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 50-2106. A duplicate copy of this sheet is enclosed.

31518

PATENT TRADEMARK OFFICE

Neifeld IP Law, PC  
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Date

Respectfully submitted,

Richard A. Neifeld  
Registration No. 35,299

Printed: August 18, 2004 (1:02pm)

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Printed: May 14, 2003 (3:24pm)

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<b>NEIFELD IP LAW</b> <b>REFERENCE FORM</b> <b>LIST OF REFERENCES CITED</b> <b>BY THE APPLICANT</b> <b>(Rev: 5/14/2003)</b>	NEIFELD REF: OSEM-DB3	APPLICATION NO: 09/636,484
	FIRST NAMED INVENTOR: Walter David BRADDOCK	
	FILING DATE: 8/10/2000	GROUP ART UNIT: 2811

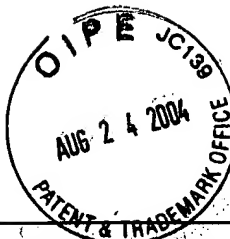
## LISTING OF UNITED STATES PATENTS - U series

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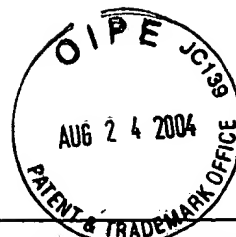
NEIFELD IP LAW REFERENCE FORM LIST OF REFERENCES CITED BY THE APPLICANT (Rev: 5/14/2003)	NEIFELD REF: OSEM-DB3	APPLICATION NO: 09/636,484
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# LISTING OF NON PATENT LITERATURE - O Series

EXAMINER INITIALS	REFERENCE NUMBER (O Series)	PUBLICATION DATE	INCLUDE IN SEQUENCE: Name of first author (in CAPITAL LETTERS), Title in quotation marks, name of publication, date of publication, page numbers, publisher, city of publication, and country of publication	ENGLISH LANGUAGE TRANSLATION ATTACHED? (YES OR NO) AND/OR OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
	O-1	4/28/1965	BECKE et al., "Gallium Arsenide Mos Transistors," Solid-State Electronics, 1965, Vol. 8, pp. 813-822, Great Britain.	No
	O-2	12/3/1995	PASSLACK et al., "C-V and G-V Characterization of In-Situ Fabricated Ga2O3-GaAs Interfaces for Inversion/Accumulati on Device and Surface Passivation Applications," Solid- State Electronics, 1996, Vol. 39, No. 8, pp. 1133-1136, Great Britain	No
	O-3	2/19/1996	PASSLACK et al., "Quasistatic and High Frequency Capacitance - Voltage Characterization of Ga2O3-GaAs Structures Fabricated by in Situ Molecular Beam Epitaxy," Appl. Phys. Lett., Feb. 19, 1996, pp. 1099-1101.	No
Date:		Examiner's Signature:		

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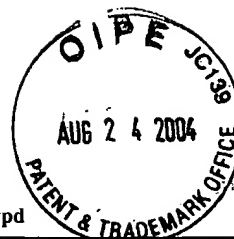
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EXAMINER INITIALS	REFERENCE NUMBER (O Series)	PUBLICATION DATE	INCLUDE IN SEQUENCE: Name of first author (in CAPITAL LETTERS), Title in quotation marks, name of publication, date of publication, page numbers, publisher, city of publication, and country of publication	ENGLISH LANGUAGE TRANSLATION ATTACHED? (YES OR NO) AND/OR IDENTIFICATION OF PRIORITY APPLICATION IN WHICH REFERENCE IS CITED
	O-4	1996	PASSLACK et al., "GaAs Surface Passivation Using in-Situ Oxide Deposition," Applied Surface Science, 1996, pp. 441-447.	No
	O-5	6/1995	PASSLACK et al., "Infrared Microscopy Studies on High-Power InGaAs-GaAs-InGaP Lasers with Ga <sub>2</sub> O <sub>3</sub> Facet Coatings," IEEE Journal of Selected Topics in Quantum Electronics, Vol. 1, No. 2, June 1995, pp. 110-115.	No
	O-6	12/15/1995	PASSLACK et al., "Capacitance - Voltage and Current - Voltage Characterization of Al <sub>x</sub> Ga <sub>1-x</sub> As - GaAs Structures," J. Appl. Phys., Vol. 78, No. 12, December 15, 1995, pp. 7091-7098	No
Date:		Examiner's Signature:		



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**LISTING OF NON PATENT LITERATURE - O Series (Continued)**

	O-7	1997	HONG et al., "Novel Ga <sub>2</sub> O <sub>3</sub> (Gd <sub>2</sub> O <sub>3</sub> ) Passivation Techniques to Produce Low Dit Oxide - GaAs Interfaces," Journal of Crystal Growth, 1997, pp. 422-427.	No
	O-8	5/1/1996	HONG et al., "Low Interface State Density Oxide-GaAs Structures Fabricated by in Situ Molecular Beam Epitaxy," J. Vac. Sci. Technol. B., Vol. 14, No. 3, May/Jun 1996, pp. 2297-2300.	No
	O-9	2/1/1997	PASSLACK et al., "Low Dit, Thermodynamically Stable Ga <sub>2</sub> O <sub>3</sub> -GaAs Interfaces: Fabrication, Characterization, and Modeling," IEEE Transactions on Electron Devices, Vol. 44, No. 2, February 1997, pp. 214-225.	No
Date:		Examiner's Signature:		